

Part Number

Customer

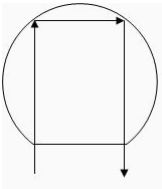
Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.30 mm	
	2.0	Primary Flat Orientation	<110> +/- 1 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	semi std/none	
	5.0	Overall Thickness	1,443.00 +/- 51.00 µm	Sum of individual layers, guaranteed by process.
	6.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	7.0	Bow	<80.00µm	ESTIMATE ONLY - ADE to ASTM F534, 20% Best effort not guaranteed
	8.0	Warp	<80.00µm	ESTIMATE ONLY - ADE to ASTM F657, 20% Best effort not guaranteed
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	13.0	Handle Thickness	700.00 +/- 25.00 µm	ADE, 100%
	14.0	Handle Doping Type	P	Wafer Vendor
	15.0	Handle Dopant	Boron	Wafer Vendor
	16.0	Handle Resistivity	0.1 - 1 Ohmcm	Wafer Vendor
	17.0	Backside Finish	Polished with laser mark and oxide.	Guaranteed by process
DeviceSilicon	18.0	Device Growth Method	CZ	Wafer Vendor
	19.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor
	20.0	Nominal Thickness	700.00 +/- 25.00 µm	ADE, 100%
	21.0	Device Doping Type	P	Wafer Vendor
	22.0	Device Dopant	Boron	Wafer Vendor
	23.0	Device Resistivity	0.1- 1 Ohmcm	Wafer Vendor
BuriedOxide	24.0	Oxide Type	Thermal	Guaranteed by process
	25.0	Oxide formed on	Handle and / or Device Layer	Guaranteed by process
	26.0	Oxide Thickness	30,000.00 +/- 3,000.00 Å	n
DeviceSilicon2	27.0	Device 2 Growth Method	CZ	Wafer Vendor
	28.0	Device 2 Orientation	{100} +/- 1 degree	Wafer Vendor
	29.0	Device 2 Nominal Thickness	40.00 +/- 1.00 µm	Filmetrics, 9point. 100%
	30.0	Device 2 DopingType	P	W
	31.0	Device 2 Dopant	Boron	W
	32.0	Device 2 Resistivity	0.002 - 0.01 Ohm cm	Wafer Vendor

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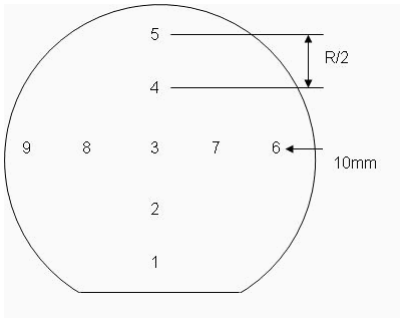
Category		Parameter	Specification	Measurement Method
DeviceSilicon2	33.0	Device 2 Voids	None	Bright Light Inspection, 100%
	34.0	Device 2 Haze	None	Bright Light Inspection, 100%

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Category	Parameter	Specification	Measurement Method
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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.		
	3. 9 point measurement are as shown in the diagram below:		



Additional Information